TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

T6C63

COLUMN DRIVER FOR A DOT MATRIX LCD

The T6C63 is a 240-channel-output column driver for an STN dot matrix LCD.

The T6C63 features a 42-V LCD drive voltage and a 20-MHz maximum operating frequency. The T6C63 is able to drive LCD panels with a duty ratio of up to 1 / 480. It is recommended for use with the T6C14.

:240

FEATURES

- Display duty application : to 1/480
- LCD drive signal
- Data transfer
- Operating frequency
- LCD drive voltage
- Power supply voltage $\therefore 2.7$ to 5.5 V
- Operating temperature : −20 to 75°C
- LCD drive output resistance: 700Ω (typ.), 1200Ω (max) (20 V, 1 / 13 bias)

: 8-bit bidirectional

: 20 MHz (V_{DD} = 4.5 V)

: 14 to 42 V (max 45 V)

 $12.5 \text{ MHz} (\text{V}_{\text{DD}} = 2.7 \text{ V})$

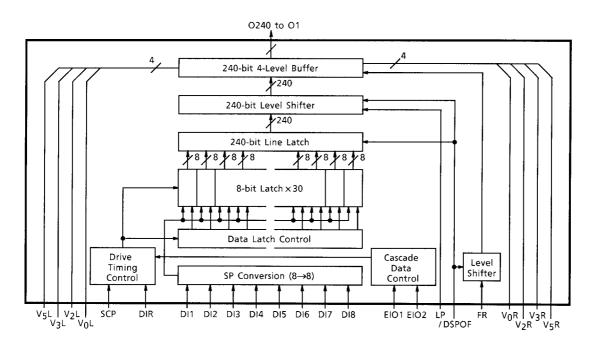
- Display-off function
- : When / DSPOF is L, all LCD drive outputs (O1 to O240) remain at the V5 level. • Low power consumption : Cascade connection and auto enable transfer functions are available.

			Unit: mm				
T6C63		Lead Pitch					
16063	'	IN	OUT				
(UAN, 31	1 5)	0.60	0.074				
	deale	t Toshiba or an r for informatior					

TCP (Tape Carrier Package)

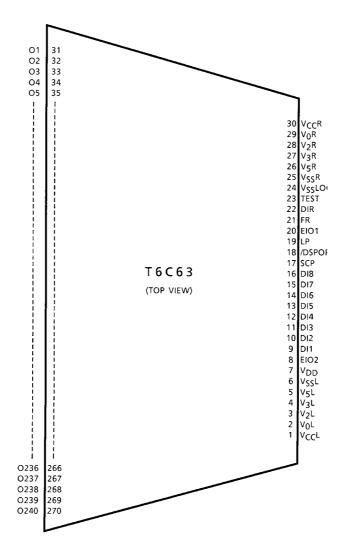
TOSHIBA

BLOCK DIAGRAM



TOSHIBA

PIN ASSIGNMENT



The above diagram shows the pin configuration of the LSI Chip, not that of the tape carrier package.

TOSHIBA

PIN FUNCTIONS

PIN NAME	1/0	FUNCTIONS	LEVEL
O1 to O240	Output	Output for LCD drive signal	V_0 to V_5
EIO1, EIO2	1/0	Input / output for enable signal DIR selects In or Out. Connect EIO (IN) of 1st LSI to L. For a cascade connection, connect EIO (OUT) to EIO (IN) of next LSI When DIR is high level, refer to as below. SCP rising edge that input after falling edge of EIO1(IN) is set to be enable. At SCP 20th clock, all 160-bit data latched. When EIO2 (OUT) is disenable, it is always set to high level. In SCP rising edge to next SCP rising edge after 20th clock from chip enable, it is set to low level.	
DI1 to DI8	Input	Input for data signal	
DIR	Input	(Direction) Input for data flow direction select	
/ DSPOF	Input	(Display off) / DSPOF = L: Display-off mode, (O1 to O240) remain at the V ₅ level / DSPOF = H: Display-on mode, (O1 to O240) are operational.	V_{DD} to V_{SS}
LP	Input	(Latch pulse) Display data is latched on falling edges of LP. When EIO (IN) = L, SCP·LP = H enables the 1st LSI. When EIO (IN) is fixed to low level, 1st LSI in cascade connection is latched chip enable at /SCP LP = high level.	
FR	Input	(Frame) Input for frame signal	
SCP	Input	(Shift clock pulse) Input for shift clock pulse	
TEST	_	(Test) Fix to L or open	
V _{DD}	_	Power supply for internal logic (5.0 V)	
V _{SS} LOG	_	Power supply for internal logic (0 V)	
V _{SS} L·R	—	Power supply for LCD drive circuit	
V ₅ L·R	—	Power supply for LCD drive circuit	_
V _{3/4} L·R	—	Power supply for LCD drive circuit	
V _{2/1} L·R	—	Power supply for LCD drive circuit	
V ₀ L·R	_	Power supply for LCD drive circuit	
V _{CC} L·R	—	Power supply for LCD drive circuit	

<u>TOSHIBA</u>

RELATION BETWEEN FR, DATA INPUT AND OUTPUT LEVEL

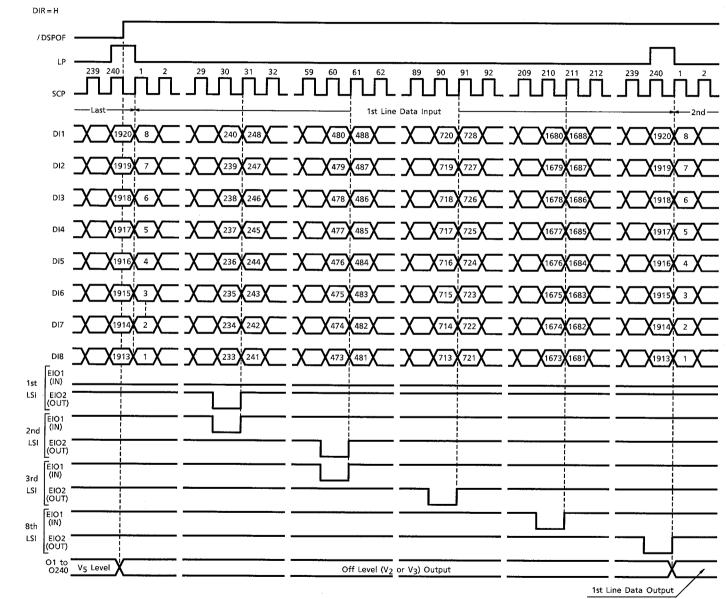
FR	DATA INPUT (DI1 to DI8)	/ DSPOF	OUTPUT LEVEL
н	L	Н	V ₂
Н	Н	Н	V ₀
L	L	Н	V ₃
L	Н	Н	V ₅
—	_	L	V ₅

DATA INPUT FORMAT

ENABLE PIN	LE PIN	(**4)	INPUT DATA LINE AND OUTPUT BUFFERS								
DIR	(EIO1)	(EIO2)	(*1)	DI1	DI2	DI3	DI4	DI5	DI6	DI7	DI8
н	H IN OUT	OUT	L	O240	O239	O238	O237	O236	O235	O234	O233
		001	F	O8	07	O6	O5	04	O3	O2	O1
	L OUT IN		L	01	O2	O3	04	O5	O6	07	O8
L		IIN	F	O233	O234	O235	O236	O237	O238	O239	O240

*1 : L: Last Data F: First Data

TIMING DIAGRAM



T6C63-6

T6C63

ABSOLUTE MAXIMUM RATINGS (Ensure that the following conditions are maintained: $V_{CC} \ge V_0 \ge V_2 \ge V_3 \ge V_5 \ge V_{SS}$)

ITEM	SYMBOL	PIN NAME	RATING	UNIT
Supply Voltage 1	V _{DD}	V _{DD}	-0.3 to 6.5	
Supply Voltage 2	V _{CC}	V _{CC} L / R	-0.3 to 45.0	
Supply Voltage 3	V ₀ , V ₂	V ₀ L / R, V _{2, 1} L / R	-0.3 to V _{CC} + 0.3	V
Supply Voltage 4	V ₃ , V ₅	V _{3, 4} L / R, V ₅ L / R	-0.3 to V _{CC} + 0.3	
Input Voltage	V _{IN}	(*2)	-0.3 to V _{DD} + 0.3	
Operating Temperature	T _{opr}	_	-20 to 75	°C
Storage Temperature	T _{stg}	-	-40 to 125	J

*2: SCP, FR, LP, DIR, EIO1, EIO2, DI1 to DI8, / DSPOF, TEST

ELECTRICAL CHARACTERISTICS DC CHARACTERISTICS (Unless Otherwise Noted, $V_{SS} = 0V$, $V_{DD} = 2.7$ to 5.5 V, Ta = -20 to 75°C)

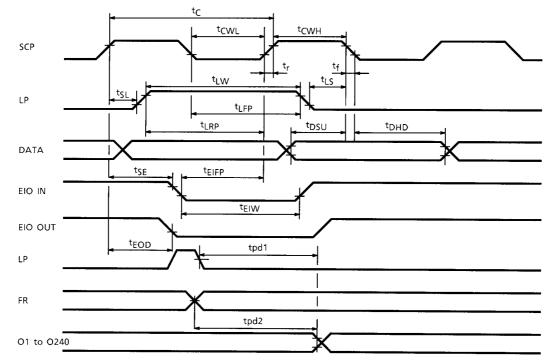
ITE	М	SYMBOL	TEST CIR- CUIT	TEST CONDITION			MIN	TYP.	MAX	UNIT	PIN NAME		
Supply Volta	Supply Voltage 1 V _{DD}		_	—			2.7	5.0	5.5		V _{DD}		
Supply Volta	ge 2	V _{CC}	-		_	_		14.0	_	42.0		V _{CC} L / R	
Input	H Level	V _{IH}			-	_		0.8 V _{DD}		V _{DD}		SCP, FR, LP, DIR, EIO1, EIO2, DI1	
Voltage	L Level	V _{IL}		_				0		0.2 V _{DD}	V	to DI8, / DSPOF, TEST	
Output Voltage	H Level	V _{OH}	_	I _{OH} = −0.5 mA			V _{DD} -0.5	_	VDD		EIO1 EIO2		
voltage	L Level	V _{OL}		I _{OL} = 0.5 mA				0	-	0.5			
	H Level	R _{OH}		V _{OUT} = V ₀ - 0.5 V (*3			(*3)	_	700	1200	I		
Output	M Level	R _{OM}		V _{OUT} =	$V_{OUT} = V_2 \pm 0.5$		(*3)	—	700	1200	Ω	O1 to O240	
Resistance		R _{OM}		V _{OUT} = V ₃ ± 0.5 V		(*3)	—	700	1200	52	01100240		
	L Level	R _{OL}	_	V _{OUT} =	V ₅ + 0.5	V	(*3)	—	700	1200			
Input Curren	t	Ι _{ΙĽ}		V _{DD} 5.0			ON	-10		10	μΑ	V ₀ L / R V ₂ L / R V ₃ L / R V ₅ L / R	
		IDD Ope		5.0		Function	(*4)	_	_	5.0			
				2.7			(*4)	—	—	2.5	mA	V _{DD}	
Current Consumptior	ı	I _{DD} St / by] —	5.0	20	Function	(*5)	_	_	2.0		עטי	
	Concernption			2.7		Function	(*5)	_	_	1.0			
		I _{CC} Leak		5.0	42	Standby		-10	—	10	μA	V _{CC} L / R	

*3 : V_{CC} = 20 V, 1 / 13 bias

*4 : f_{scp} = 13 MHz, f_{LP} = 54 kHz, f_{FR} = 13.5 kHz, f_{EIO} = 650 kHz Data Format: every bit inverted, while internal data receriver is operating

*5 : f_{scp} = 13 MHz, f_{LP} = 54 kHz, f_{FR} = 13.5 kHz Data Format: every bit inverted, Internal data receriver is sleeping

AC ELECTRICAL CHARACTERISTICS



TEST CONDITIONS (1) (Unless Otherwise Noted, $V_{SS} = 0 V$, $V_{DD} = 4.5$ to 5.5 V, $V_{CC} = 14$ to 42 V, Ta = -20 to 75°C)

ITEM	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Clock Cycle	t _C	—	50	—	_	
SCP Pulse Width	t _{CWH} , t _{CWL}	—	10	—	_	
Data Set-Up Time	t _{DSU}	—	8	—	_	
Data Hold Time	t _{DHD}	—	10	—	_	
SCP Rise / Fall Time	t _r , t _f	—	—	—	(*6)	
LP Rise Time	t _{LRP}	—	11	—	_	
LP Fall Time	t _{LFP}	—	7	—	_	
LP Pulse Width	t _{LW}	—	7	—	_	
SCP-to-LP Delay Time (SLP \rightarrow LP)	t _{SL}	—	0	—	_	ns
LP-to-SCP Delay Time (LP \rightarrow SCP)	t _{LS}	—	7	—	_	
EIO IN Rise Time	t _{EIFP}	—	20	—	_	
EIO IN Pulse Width	t _{EIW}	—	9	—	_	
SCP-to-EIO Delay Time (SCP \rightarrow EIO)	t _{SE}	—	1	—	_	
EIO-OUT Delay Time	t _{EOD}	(*7)	—	—	20	
Output Delay Time 1 (LP \rightarrow OUT)	t _{pd1}	—	—	—	400	
Output Delay Time 2 (FR \rightarrow OUT)	t _{pd2}	—	—	_	400	
Output Delay Time Variation	(*8)	_	—	0	30	

*6 : t_r , $t_f \le (t_C - t_{CWH} - t_{CWL}) / 2$ and t_r , $t_f \le 50$ ns

*7 : C_L = 10 pF

*8 : Variation between output pins in t_{pd1} and t_{pd2} .

TEST CONDITIONS (2) (Unless Otherwise Noted, $V_{SS} = 0 V$, $V_{DD} = 2.7$ to 4.5 V, $V_{CC} = 14$ to 42 V, Ta = -20 to 75°C)

ITEM	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Clock Cycle	t _C	_	80	—	—	
SCP Pulse Width	t _{CWH} , t _{CWL}	—	20	_	—	
Data Set-Up Time	t _{DSU}	—	15	_	—	
Data Hold Time	t _{DHD}	—	10	_	—	
SCP Rise / Fall Time	t _r , t _f	—	—	_	(*9)	
LP Rise Time	t _{LRP}	_	15	_	—	
LP Fall Time	tLFP	—	14	—	—	
LP Pulse Width	t _{LW}	—	14	_	—	
SCP-to-LP Delay Time	t _{SL}	—	2	—	—	ns
LP-to-SCP Delay Time	t _{LS}	—	14	_	—	
EIO IN Fall Time	t _{EIFP}	—	20	_	—	
EIO IN Pulse Width	t _{EIW}	—	14	_	—	
SCP-to-EIO Delay Time	t _{SE}	—	2	_	—	
EIO-OUT Delay Time	t _{EOD}	(*10)	—	—	36	
Output Delay Time 1 (LP \rightarrow OUT)	t _{pd1}	—	—	—	500	
Output Delay Time 2 (FR \rightarrow OUT)	t _{pd2}	—	—	—	500	
Output Delay Time Variations	(*11)	_	—	0	50	

*9 : t_r , $t_f \le (t_C - t_{CWH} - t_{CWL}) / 2$ and t_r , $t_f \le 50$ ns

*10 : C_L = 10 pF

*11 : Variation between output pins in t_{pd1} and t_{pd2}

NOTE: Insert the bypass capacitor (0.1 μ F) between V_{DD} and V_{SS}, and between V_{CC} and V_{SS} to decrease power supply noise.

Place the bypass capacitor as close to the LSI as possible.

RESTRICTIONS ON PRODUCT USE

Handbook" etc..

000707EBE

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- Polyimide base film is hard and thin. Be careful not to injure yourself on the film or to scratch any other parts with the film. Try to design and manufacture products so that there is no chance of users touching the film after assembly, or if they do, that there is no chance of them injuring themselves. When cutting out the film, try to ensure that the film shavings do not cause accidents. After use, treat the leftover film and reel spacers as industrial waste.
- Light striking a semiconductor device generates electromotive force due to photoelectric effects. In some cases this can cause the device to malfunction.
 This is especially true for devices in which the surface (back), or side of the chip is exposed. When designing circuits, make sure that devices are protected against incident light from external sources. Exposure to light both during regular operation and during inspection must be taken into account.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.